

# EE 207 Worked Solutions Spring Session 2006-07

1)  
Charge neutrality condition:

$$n + N_a = p + N_d$$

Also  $np = n_i^2$  (2)

$$\therefore n^2 - (N_d - N_a)n - n_i^2 = 0$$

$$n = \frac{N_d - N_a}{2} + \frac{N_d - N_a}{2} \left[ 1 + \left( \frac{2n_i}{N_d - N_a} \right)^2 \right]^{1/2}$$

1) For n-type extrinsic semiconductor,  $N_d - N_a \gg n_i$ , so above is

$$n = N_d - N_a \approx N_d$$

since  $p = \frac{n_i^2}{n} = \frac{n_i^2}{N_d - N_a} = \frac{n_i^2}{N_d}$  (2)

2) For near compensated case,  $n_i \gg N_d - N_a$ , so above is

$$n \approx n_i + \frac{N_d - N_a}{2} \approx n_i$$

$$p = \frac{n_i^2}{n} \approx n_i$$
 (2)

[6]

0) Intrinsic conductivity,  $\sigma_i = \frac{1}{\rho_i} = n_i e (\mu_e + \mu_h)$

$$\frac{1}{5 \times 10^3} = 2 \times 10^{-4} = n_i \times 1.6 \times 10^{-19} (0.12 + 0.05) = n_i \times 2.72 \times 10^{-19}$$

$$n_i = \frac{2 \times 10^{-4}}{2.72 \times 10^{-19}} = 7.35 \times 10^{15} \text{ m}^{-3}$$
 (3)

With initial n-doping only,  $p_i^*$  is  $10^{-4} p_i^* = 10^{-4} \times 5 \times 10^3 = 0.5$

Since n-doped, ignore  $n_i$ , so

$$\frac{1}{p} \approx n_d \mu_e \Rightarrow \frac{1}{0.5} = 2 = 1.6 \times 10^{-19} \times N_d \times 0.12$$

$$\therefore N_d = 1.04 \times 10^{20} \text{ m}^{-3}$$
 (3)(2)

\* Doping can only reduce resistivity c.f. intrinsic value.

After compensation,  $\rho = 7.61 \times 10^{-2} \Omega\text{-m}$   
 For compensated case,

$$\frac{1}{\rho} = \sigma = e(n\mu_e + p\mu_h) = e(n\mu_e + \frac{n_i^2}{n}\mu_h)$$

$$\frac{1}{7.61 \times 10^{-2}} = 1.314 \times 10^{-3} = 1.6 \times 10^{-19} \left[ n \times 0.12 + \left( \frac{7.35 \times 10^{15}}{n^2} \right)^2 \times 0.05 \right]$$

$$n^2 - 6.84 \times 10^{16} n + 2.25 \times 10^{31} = 0$$

$$n = \frac{6.84 \times 10^{16} \pm \sqrt{(6.84 \times 10^{16})^2 - 4 \times 2.25 \times 10^{31}}}{2}$$

$$n = 6.81 \times 10^{16} \text{ or } 3.2 \times 10^{14}$$

$n$  must be  $> n_i$ , so  $n = 6.81 \times 10^{16} \text{ m}^{-3}$  *lot of work*

$$p = \frac{n_i^2}{n} = \frac{(7.35 \times 10^{15})^2}{6.81 \times 10^{16}} = 7.93 \times 10^{14} \text{ m}^{-3}$$

(2) (3)?

*one makes for these workings? wrap?*

We need  $N_a$ : From charge neutrality,

$$N_a = p + N_d - n = 7.93 \times 10^{14} + 1.04 \times 10^{20} - 6.81 \times 10^{16} \\ = 1.039 \times 10^{20} \text{ m}^{-3}$$

(2)

[10]

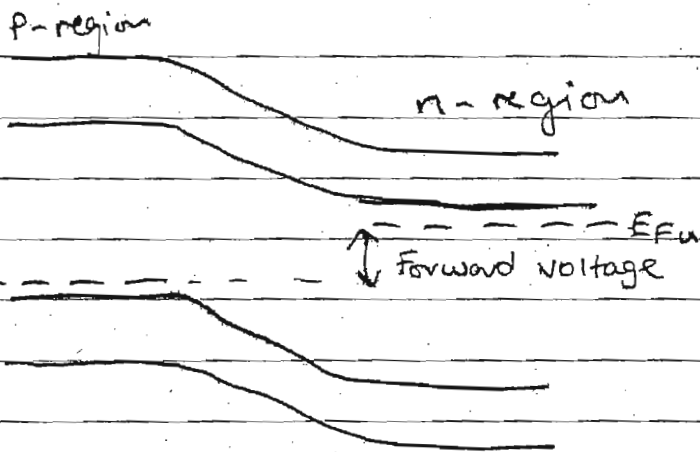
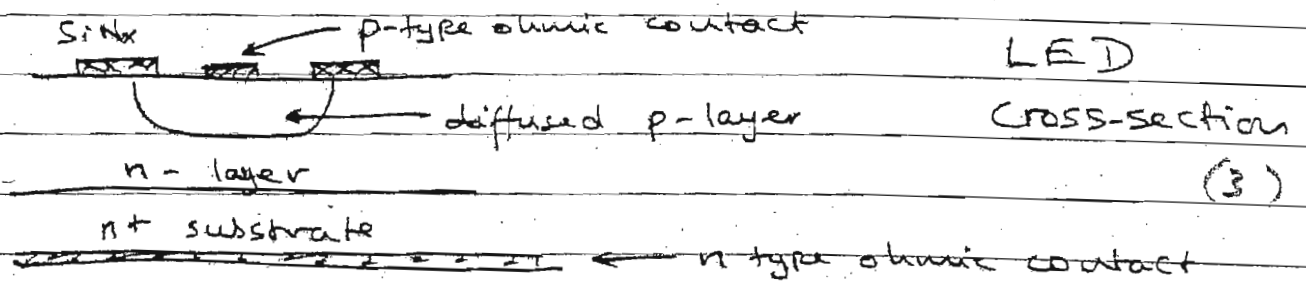
c) To get back original resistivity requires slightly more acceptor doping. The doping control required for this to happen makes this impossible in practice.

*is this right?*

[4]

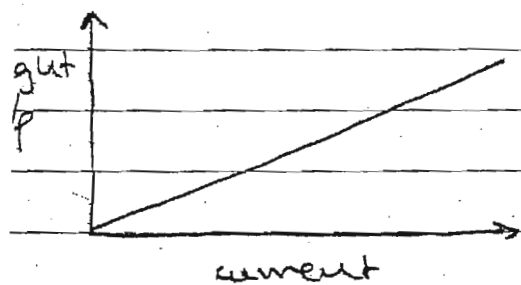
22

a)



Band diagram under LED emission

(3)



light output increases ~ linearly (2) with injection current. In a laser, there will be a region of very small increase initially, before a sudden increase at the threshold condition

[8]

b) The range of wavelengths is given by the bulk GaAs band-gap to that of the AlGaAs barrier, i.e.

$$\lambda_{\max} = \frac{1.24}{1.42} = 0.87 \mu\text{m}$$

$$\lambda_{\min} = \frac{1.24}{1.85} = 0.67 \mu\text{m}$$

[3]

c) Operating wavelength = 850 nm  $\equiv \frac{1.24}{0.85} = 1.46 \text{ eV}$

$$E_n = \frac{n^2 h^2}{8 m^* L^2} ; n=1, m_e^* = 0.063 m_0, m_h^* = 0.48 m_0$$

$$\text{Total band-gap} = 1.42 + E_{\text{elect.}} + E_{\text{hole}} \quad (3)$$

$$E_{\text{elect}} = \frac{(6.63 \times 10^{-34})^2}{8 \times 0.063 \times 9.11 \times 10^{-31} \times 1.6 \times 10^{-19}} \cdot \frac{1}{L^2} \text{ eV}$$

$$E_{\text{hole}} = \frac{(6.63 \times 10^{-34})^2}{8 \times 0.48 \times 9.11 \times 10^{-31} \times 1.6 \times 10^{-19}} \cdot \frac{1}{L^2} \text{ eV}$$

$$1.46 = 1.42 + \frac{6.768 \times 10^{-18}}{L^2} \quad (3)$$

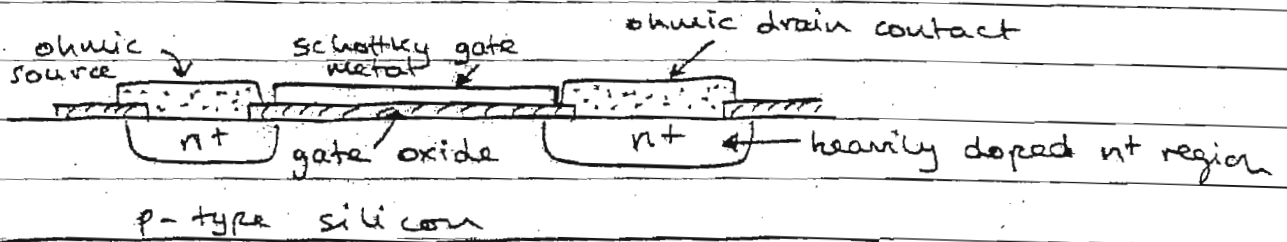
$$L = 1.3 \times 10^{-8} \text{ m} \quad \text{or} \quad 13 \text{ nm} \quad [6]$$

d) In reality, as the QW dimension reduces, the onset of tunnelling through the finite barriers will limit the minimum wavelength.

[3]

23

(a)



[4]

$$b) \quad I_d = \frac{\mu_e C_g}{l^2} \left[ V_s - V_T - \frac{V_d}{2} \right] V_d$$

Saturation occurs when  $V_d = V_g - V_T$ ,  $\therefore I_{ds}$  is

$$= \frac{\mu_e C_g}{l^2} \frac{V_d^2}{2} \quad (2)$$

$g_m = \frac{\partial I_d}{\partial V_g} \Big|_{V_d}$  in saturation region, so differentiate above

$$\therefore g_m = \frac{\mu_e C_g}{l^2} V_d \quad (2)$$

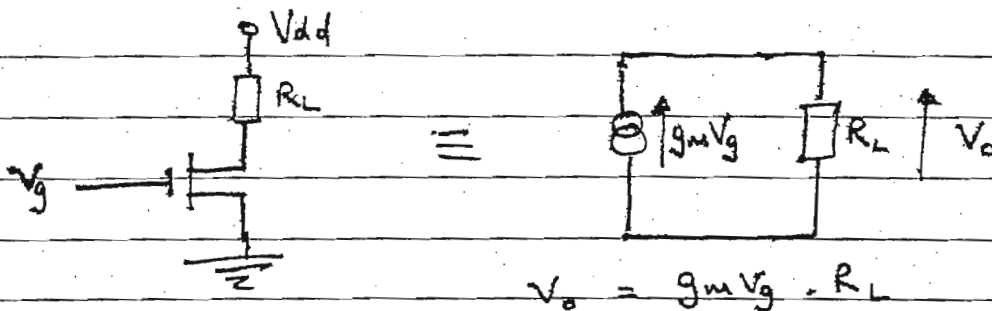
Rearrange and substitute into expression of  $I_{ds}$

$$\frac{\mu_e C_g}{l^2} = \frac{g_m}{V_d} = \frac{2 I_{ds}}{V_d^2}$$

$$\therefore g_m = \frac{2 I_{ds}}{V_d} \quad (1)$$

[5]

(c)



$$\text{Gain} = \frac{V_o}{V_g} = |A| = g_m R_L \quad (2)$$

$$\therefore 30 = g_m R_L = \frac{2 I_{ds}}{V_d} \cdot R_L = \frac{2 I_{ds} \cdot R_L}{(V_{dd} - I_{ds} R_L)} \quad (3)$$

out.  $30 = \frac{2 \times 30 \times 10^{-3} R_L}{100 - 30 \times 10^{-3} R_L}$

gives  $R_L = 3.125 \text{ k}\Omega$

(2)

[7]

d)  $g_m = 9.6 \text{ mS} = \frac{\mu_e C_g V_d}{l^2}$

$$l^2 = \frac{\mu_e C_g V_d}{g_m} = \frac{0.13 \times 10^{-12} \times 6.25}{9.6 \times 10^{-3}}$$

$l = 9.2 \mu\text{m}$  (gate length)

$$C_g = \frac{\epsilon_0 \epsilon_r \text{Area}}{t_o} = \frac{\epsilon_0 \epsilon_r \cdot l \cdot \text{width}}{t_o}$$

length = 0.1 width  $\Rightarrow$  width =  $92 \mu\text{m}$

$$t_o = \frac{\epsilon_0 \epsilon_r \cdot l \cdot \text{width}}{C_g} = \frac{11.8 \times 8.85 \times 10^{-12} \times 9.2 \mu\text{m} \times 92 \mu\text{m}}{10^{-12}}$$

$t = 88 \text{ nm}$

[4]

24

$$a) \quad E = hf, \quad c = f\lambda$$

$$= \frac{hc}{\lambda}$$

$$\lambda = \frac{hc}{E} \quad \text{where } E \text{ is in joules}$$

To get  $E$  in eV, divide numerator + denominator by 'e'

$$\therefore \lambda = \left( \frac{hc}{e} \right) / (E/e)$$

$$\therefore \lambda = \frac{hc}{e} = 1.24 \mu\text{m eV}$$

[4]

$$i) \text{ de Broglie: } p = mv = \frac{h}{\lambda} \quad (3)$$

$h$  = Planck's constant,  $m$  = mass,  $v$  = velocity,  $\lambda$  = wavelength

Equate K.E. to P.E

$$\frac{1}{2}mv^2 = eV \Rightarrow v = \left( \frac{2eV}{m} \right)^{1/2}$$

$$\text{From de Broglie, } mv = \frac{h}{\lambda}$$

(3)

$$\lambda = \frac{h}{mv} = \frac{h}{(2eVm)^{1/2}} = \frac{1.225 \text{ nm}}{\sqrt{V}} = \frac{1.225 \text{ nm}}{6}$$

$= 0.204 \text{ nm}$ , which is the minimum resolvable size.

[6]

$$(c) \quad E = E_g + Ak^2 + Bk^4$$

$$m^* = \left( \frac{d^2 E}{dp^2} \right)^{-1}, \quad p = \hbar k$$

$$m^* = \hbar^2 \left( \frac{d^2 E}{dk^2} \right)^{-1}$$

(2)

$$\text{cont. } \frac{dE}{dk} = 2Ak + 4Bk^3, \quad \frac{d^2E}{dk^2} = 2A + 12Bk^2$$

$$\begin{aligned} \text{At } k=0, m^* &= \hbar^2 (2A + 0)^{-1} = \left[ \frac{6.626 \times 10^{-34}}{2\pi} \right]^2 [2 \times 10^{-38}]^{-1} \\ &= 5.56 \times 10^{-31} \\ &= 0.61 m_0 \end{aligned} \quad (3)$$

) At Brillouin zone edge,  $v_g = 0$

$$v_g = \frac{dE}{dp} = \frac{1}{\hbar} \cdot \frac{dE}{dk} = \frac{1}{\hbar} (2Ak + 4Bk^3) = 0$$

$$Ak + 2Bk^3 = 0 \Rightarrow k = \left[ \frac{A}{-2B} \right]^{1/2} \quad (B \text{ is -ive so } \sqrt{\text{OK}})$$

$$\text{Need } m^* @ k = \left[ \frac{A}{-2B} \right]^{1/2}$$

$$m^* = \frac{\hbar^2}{2A + 12Bk^2} = \frac{\hbar^2}{2A + 12B \left( \frac{A}{-2B} \right)} = \frac{\hbar^2}{-4A}$$

$$= \left( \frac{6.626 \times 10^{-34}}{2\pi} \right)^2 \cdot \left( \frac{1}{-4 \times 10^{-38}} \right) = -2.78 \times 10^{-31} \quad (5)$$

$$= -0.305 m_0$$

[10]

But tricky!